

**FEATURES**

**5Ω Max On Resistance**  
**0.5Ω Max On Resistance Flatness**  
**33 V Supply Maximum Ratings**  
**Fully specified at ±15V/12V/±5V**  
**3V Logic Compatible Inputs**  
**Rail-to-Rail Operation**  
**Break-Before-Make Switching Action**  
**16-Lead TSSOP Packages**  
**Typical Power Consumption (< 0.03 μW)**

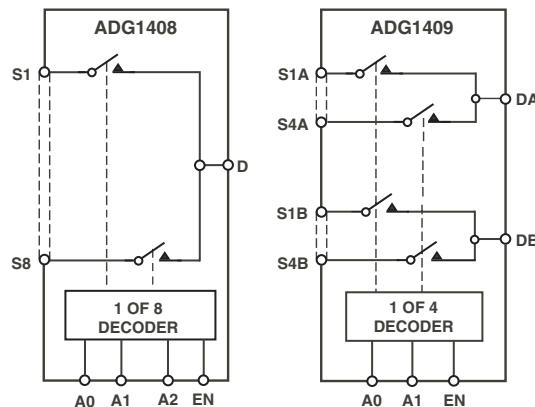
**APPLICATIONS**

**Relay Replacement**  
**Audio and Video Routing**  
**Automatic Test Equipment**  
**Data Acquisition Systems**  
**Battery-Powered Systems**  
**Sample-and-Hold Systems**  
**Communication Systems**

**GENERAL DESCRIPTION**

The ADG1408 and ADG1409 are monolithic CMOS analog multiplexers comprising eight single channels and four differential channels, respectively. The ADG1408 switches one of eight inputs to a common output as determined by the 3-bit binary address lines A0, A1, and A2. The ADG1409 switches one of four differential inputs to a common differential output as determined by the 2-bit binary address lines A0 and A1. An EN input on both devices is used to enable or disable the device. When disabled, all channels are switched OFF.

The ADG1408/ADG1409 are designed on an enhanced CMOS process that provides low power dissipation yet gives high switching speed and low on resistance. Each channel conducts equally well in both directions when ON and has an input signal range that extends to the supplies. In the OFF condition, signal levels up to the supplies are blocked. All channels exhibit break-before-make switching action, preventing momentary shorting when switching channels. Inherent in the design is low charge injection for minimum transients when switching the digital inputs.

**FUNCTIONAL BLOCK DIAGRAMS**


SWITCHES SHOWN FOR A "1" LOGIC INPUT

**PRODUCT HIGHLIGHTS**

1. 5Ω Max On Resistance
2. 0.5Ω Max On Resistance Flatness
3. 3V Logic Compatible Digital Input  
 $V_{IH} = 2.0V$ ,  $V_{IL} = 0.8V$
4. 16 Lead TSSOP package

**RevPrA**

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**REVISION HISTORY**

## ADG1408/ADG1409—SPECIFICATIONS

DUAL SUPPLY<sup>1</sup>Table 1.  $V_{DD} = +15\text{ V} \pm 10\%$ ,  $V_{SS} = -15\text{ V} \pm 10\%$ ,  $GND = 0\text{ V}$ , unless otherwise noted.

Parameter	-40°C to		-40°C to +125°C	Unit	Test Conditions/Comments
	+25°C	+85°C			
ANALOG SWITCH					
Analog Signal Range			$V_{SS}$ to $V_{DD}$	V	
$R_{ON}$	3			$\Omega$ typ	$V_D = \pm 10\text{ V}$ , $I_S = -10\text{ mA}$
	4	5	5	$\Omega$ max	
$R_{ON}$ Flatness				$\Omega$ typ	$V_D = +10\text{ V}$ , $-10\text{ V}$
	0.5			$\Omega$ max	
$\Delta R_{ON}$	0.5			$\Omega$ typ	$V_D = +10\text{ V}$ , $-10\text{ V}$
				$\Omega$ max	
LEAKAGE CURRENTS					
Source OFF Leakage $I_S$ (OFF)	$\pm 0.01$			nA typ	$V_D = \pm 10\text{ V}$ , $V_S = -10\text{ V}$ ; Test Circuit 2
	$\pm 0.5$	$\pm 2.5$	$\pm 50$	nA max	$\pm 0.5$
Drain OFF Leakage $I_D$ (OFF)				nA max	$V_D = \pm 10\text{ V}$ ; $V_S = \pm 10\text{ V}$ ;
ADG1408	$\pm 1$	$\pm 100$	$\pm 100$	nA max	Test Circuit 3
ADG1409	$\pm 1$	$\pm 50$	$\pm 50$	nA max	
Channel ON Leakage $I_D$ , $I_S$ (ON)				nA max	$V_S = V_D = \pm 10\text{ V}$ ;
ADG1408	$\pm 1$	$\pm 100$	$\pm 100$	nA max	Test Circuit 4
ADG1409	$\pm 1$	$\pm 50$	$\pm 50$	nA max	
DIGITAL INPUTS					
Input High Voltage, $V_{INH}$		2.0	2.0	V min	
Input Low Voltage, $V_{INL}$		0.8	0.8	V max	
Input Current				$\mu\text{A}$ max	$V_{IN} = V_{INL}$ or $V_{INH}$
$I_{INL}$ or $I_{INH}$	$\pm 0.005$	$\pm 0.5$	$\pm 0.5$	$\mu\text{A}$ max	
$C_{IN}$ , Digital Input Capacitance	5			pF typ	
DYNAMIC CHARACTERISTICS <sup>2</sup>					
$t_{TRANSITION}$	80	120	120	ns typ	$R_L = 300\ \Omega$ , $C_L = 35\text{ pF}$ ;
		250	250	ns max	$V_{S1} = \pm 10\text{ V}$ , $V_{S8} = \pm 10\text{ V}$ ;
$T_{BBM}$	10	10	10	ns typ	Test Circuit 5
			1	ns min	$R_L = 300\ \Omega$ , $C_L = 35\text{ pF}$ ;
$t_{ON}(EN)$	85	125	125	ns typ	$V_S = 10\text{ V}$ ; Test Circuit 6
	150	225	225	ns max	$R_L = 300\ \Omega$ , $C_L = 35\text{ pF}$ ;
$t_{OFF}(EN)$	40	65	65	ns typ	$V_S = 5\text{ V}$ ; Test Circuit 7
		150	150	ns max	$R_L = 300\ \Omega$ , $C_L = 35\text{ pF}$ ;
Charge Injection	20		20	pC typ	$V_S = 0\text{ V}$ , $R_S = 0\ \Omega$ , $C_L = 10\text{ nF}$ ; Test Circuit 8
OFF Isolation	75			dB typ	$R_L = 1\text{ k}\Omega$ , $f = 100\text{ kHz}$ ;
Channel-to-Channel Crosstalk	85			dB typ	$V_{EN} = 0\text{ V}$ ; Test Circuit 9
					$R_L = 1\text{ k}\Omega$ , $f = 100\text{ kHz}$ ;
Total Harmonic Distortion, THD + N	0.002			% typ	Test Circuit 10
					$R_L = 600\ \Omega$ , $5V_{rms}$ ; $f = 20\text{ Hz}$ to $20\text{ kHz}$
-3dB Bandwidth	50			MHz typ	$R_L = 300\ \Omega$ , $C_L = 5\text{ pF}$ ; Test Circuit 10
					Test Circuit 10
$C_S$ (OFF)	15			pF typ	$f = 1\text{ MHz}$
$C_D$ (OFF)					$f = 1\text{ MHz}$

Parameter	-40°C to		Unit	Test Conditions/Comments
	+25°C	+85°C		
ADG1408	100		pF typ	f = 1 MHz
ADG1409	50		pF typ	
C <sub>D</sub> , C <sub>S</sub> (ON)				
ADG1408	150		pF typ	
ADG1409	75		pF typ	
<b>POWER REQUIREMENTS</b>				
I <sub>DD</sub>	0.001		μA typ	V <sub>DD</sub> = +16.5V, V <sub>SS</sub> = -16.5V Digital Inputs= 0 V or V <sub>DD</sub>
		5	μA max	
I <sub>DD</sub>	150		μA typ	Digital Inputs= 5 V
			μA max	
I <sub>SS</sub>	0.001		μA typ	Digital Inputs= 0 V or V <sub>DD</sub>
		5	μA max	
I <sub>GND</sub>	0.001		μA typ	Digital Inputs= 0 V or V <sub>DD</sub>
		5	μA max	
I <sub>GND</sub>	150		μA typ	Digital Inputs= 5 V
		5	μA max	
			μA max	

<sup>1</sup> Temperature ranges are as follows: B Version: -40°C to +85°C; T Version: -40°C to +125°C.

<sup>2</sup> Guaranteed by design, not subject to production test.

## SINGLE SUPPLY<sup>1</sup>

**Table 2.** V<sub>DD</sub> = 12 V V ± 10%, V<sub>SS</sub> = 0 V, GND = 0 V, unless otherwise noted.

Parameter	+25°C	-40°C to +85°C	-40°C to +125°C	Unit	Test Conditions/Comments
<b>ANALOG SWITCH</b>					
Analog Signal Range			0 to V <sub>DD</sub>	V	
R <sub>ON</sub>	6			Ω typ	V <sub>D</sub> = 3 V, 10 V, I <sub>S</sub> = -1 mA
	7	8	9	Ω max	
R <sub>ON</sub> Flatness				Ω typ	V <sub>D</sub> = 3 V, 10 V, I <sub>S</sub> = -1 mA
	1.5			Ω max	
ΔR <sub>ON</sub>	0.5			Ω typ	V <sub>D</sub> = 3 V, 10 V, I <sub>S</sub> = -1 mA
				Ω max	
Channel ON Leakage I <sub>D</sub> , I <sub>S</sub> (ON)					V <sub>S</sub> = V <sub>D</sub> = 8 V/0 V;
ADG1408	±1	±100	±100	nA max	Test Circuit 4
ADG1409	±1	±50	±50	nA max	
<b>DIGITAL INPUTS</b>					
Input High Voltage, V <sub>INH</sub>		2.0	2.0	V min	
Input Low Voltage, V <sub>INL</sub>		0.8	0.8	V max	
Input Current					
I <sub>INL</sub> or I <sub>INH</sub>		±10	±10	μA max	V <sub>IN</sub> = 0 or V <sub>DD</sub>
C <sub>IN</sub> , Digital Input Capacitance	8			pF typ	f = 1 MHz
<b>DYNAMIC CHARACTERISTICS<sup>2</sup></b>					
t <sub>TRANSITION</sub>	130			ns typ	R <sub>L</sub> = 300 Ω, C <sub>L</sub> = 35 pF; V <sub>S1</sub> = 8 V/0 V, V <sub>S8</sub> = 0 V/8 V; Test Circuit 5
T <sub>BBM</sub>	10			ns typ	R <sub>L</sub> = 300 Ω, C <sub>L</sub> = 35 pF;
			1	ns min	V <sub>S</sub> = 5 V; Test Circuit 6
t <sub>ON</sub> (EN)	140			ns typ	R <sub>L</sub> = 300 Ω C <sub>L</sub> = 35 pF; V <sub>S</sub> = 5 V; Test Circuit 7
t <sub>OFF</sub> (EN)	60			ns typ	R <sub>L</sub> = 300 Ω, C <sub>L</sub> = 35 pF; V <sub>S</sub> = 5 V; Test Circuit 7
Charge Injection	5			pC typ	V <sub>S</sub> = 0 V, R <sub>S</sub> = 0Ω, C <sub>L</sub> = 10 nF;

Parameter	+25°C	-40°C to +85°C	-40°C to +125°C	Unit	Test Conditions/Comments
OFF Isolation	-75			dB typ	Test Circuit 8 R <sub>L</sub> = 1 kΩ, f = 100 kHz;
Channel-to-Channel Crosstalk	85			dB typ	V <sub>EN</sub> = 0 V; Test Circuit 9 R <sub>L</sub> = 1 kΩ, f = 100 kHz;
Total Harmonic Distortion, THD + N	0.002			% typ	Test Circuit 10 R <sub>L</sub> = 600 Ω, 5Vrms; f=20Hz to 20kHz
-3dB Bandwidth	50			MHz typ	R <sub>L</sub> = 300 Ω, C <sub>L</sub> = 5 pF; Test Circuit 10
C <sub>S</sub> (OFF)	15			pF typ	f = 1 MHz
C <sub>D</sub> (OFF)					f = 1 MHz
ADG1408	100			pF typ	
ADG1409	50			pF typ	
C <sub>D</sub> , C <sub>S</sub> (ON)					f = 1 MHz
ADG1408	150			pF typ	
ADG1409	75			pF typ	
<b>POWER REQUIREMENTS</b>					V <sub>DD</sub> = 13.2V
I <sub>DD</sub>		1	1	μA typ	Digital Inputs= 0 V or V <sub>DD</sub>
		5	5	μA max	
I <sub>DD</sub>	150			μA typ	Digital Inputs= 5
			300	μA max	

<sup>1</sup> Temperature ranges are as follows: B Version: -40°C to +85°; T Version: -55°C to +125°.

<sup>2</sup> Guaranteed by design, not subject to production test.

### DUAL SUPPLY<sup>1</sup>

**Table 3. V<sub>DD</sub> = +5 V ± 10%, V<sub>SS</sub> = -5 V ± 10%, GND = 0 V, unless otherwise noted.**

Parameter	+25°C	-40°C to +85°C	-40°C to +125°C	Unit	Test Conditions/Comments
<b>ANALOG SWITCH</b>					
Analog Signal Range			V <sub>SS</sub> to V <sub>DD</sub>	V	
R <sub>ON</sub>	6			Ω typ	V <sub>D</sub> = ±3.3 V, I <sub>S</sub> = -10 mA
	7	8	10	Ω max	
ΔR <sub>ON</sub>	0.5			Ω max	V <sub>D</sub> = +3.3 V, -3.3 V
<b>LEAKAGE CURRENTS</b>					
Source OFF Leakage I <sub>S</sub> (OFF)	±0.01			nA typ	V <sub>D</sub> = ±3.3 V, V <sub>S</sub> = -3.3 V; Test Circuit 2
	±0.5	±2.5	±50	nA max	
Drain OFF Leakage I <sub>D</sub> (OFF)					V <sub>D</sub> = ±3.3 V; V <sub>S</sub> = ±3.3 V;
ADG1408	±1	±100	±100	nA max	Test Circuit 3
ADG1409	±1	±50	±50	nA max	
Channel ON Leakage I <sub>D</sub> , I <sub>S</sub> (ON)					V <sub>S</sub> = V <sub>D</sub> = ±3.3 V;
ADG1408	±1	±100	±100	nA max	Test Circuit 4
ADG1409	±1	±50	±50	nA max	
<b>DIGITAL INPUTS</b>					
Input High Voltage, V <sub>INH</sub>		2.0	2.0	V min	
Input Low Voltage, V <sub>INL</sub>		0.8	0.8	V max	
Input Current					
I <sub>INL</sub> or I <sub>INH</sub>	±0.005			μA max	V <sub>IN</sub> = V <sub>INL</sub> or V <sub>INH</sub>
		±0.5	±0.5	μA max	
C <sub>IN</sub> , Digital Input Capacitance	5			pF typ	
<b>DYNAMIC CHARACTERISTICS<sup>2</sup></b>					
t <sub>TRANSITION</sub>		120	120	ns typ	R <sub>L</sub> = 300 Ω, C <sub>L</sub> = 35 pF;

Parameter	+25°C	-40°C to +85°C	-40°C to +125°C	Unit	Test Conditions/Comments
T <sub>BBM</sub>		250	250	ns max	V <sub>S1</sub> = ±10 V, V <sub>S8</sub> = ±10 V; Test Circuit 5
				ns typ	R <sub>L</sub> = 300 Ω, C <sub>L</sub> = 35 pF;
			1	ns min	V <sub>S</sub> = 5 V; Test Circuit 6
t <sub>ON</sub> (EN)	85	125	125	ns typ	R <sub>L</sub> = 300 Ω, C <sub>L</sub> = 35 pF;
	150	225	225	ns max	V <sub>S</sub> = 5 V; Test Circuit 7
t <sub>OFF</sub> (EN)		65	65	ns typ	R <sub>L</sub> = 300 Ω, C <sub>L</sub> = 35 pF;
		150	150	ns max	V <sub>S</sub> = 5 V; Test Circuit 7
				pC typ	V <sub>S</sub> = 0 V, R <sub>S</sub> = 0 Ω, C <sub>L</sub> = 10 nF; Test Circuit 8
Charge Injection	20				
OFF Isolation	-75		-75	dB typ	R <sub>L</sub> = 1 kΩ, f = 100 kHz; V <sub>EN</sub> = 0 V; Test Circuit 9
Channel-to-Channel Crosstalk	85		85	dB typ	R <sub>L</sub> = 1 kΩ, f = 100 kHz; Test Circuit 10
Total Harmonic Distortion, THD + N	0.002			% typ	R <sub>L</sub> = 600 Ω, 5Vrms; f=20Hz to 20kHz
-3dB Bandwidth	50			MHz typ	R <sub>L</sub> = 300 Ω, C <sub>L</sub> = 5 pF; Test Circuit 10
C <sub>S</sub> (OFF)	15			pF typ	f = 1 MHz
C <sub>D</sub> (OFF)					f = 1 MHz
ADG1408	100			pF typ	
ADG1409	50			pF typ	
C <sub>D</sub> , C <sub>S</sub> (ON)					f = 1 MHz
ADG1408	150			pF typ	
ADG1409	75			pF typ	
<b>POWER REQUIREMENTS</b>					
I <sub>DD</sub>	0.001			μA typ	V <sub>DD</sub> = +16.5V, V <sub>SS</sub> = -16.5V Digital Inputs= 0 V or V <sub>DD</sub>
		5	5	μA max	
I <sub>DD</sub>	150			μA typ	Digital Inputs= 5 V
			300	μA max	
I <sub>SS</sub>	0.001			μA typ	Digital Inputs= 0 V or V <sub>DD</sub>
		5	5	μA max	
I <sub>GND</sub>	0.001			μA typ	Digital Inputs= 0 V or V <sub>DD</sub>
		5	5	μA max	
I <sub>GND</sub>	150			μA typ	Digital Inputs= 5 V
		5	300	μA max	

<sup>1</sup> Temperature ranges are as follows: B Version: -40°C to +85°C; Y Version: -40°C to +125°C.

<sup>2</sup> Guaranteed by design, not subject to production test.

**ABSOLUTE MAXIMUM RATINGS<sup>1</sup>**Table 4. Absolute Maximum Ratings ( $T_A = 25^\circ\text{C}$ , unless otherwise noted.)

Parameter	Rating
$V_{DD}$ to $V_{SS}$	36 V
$V_{DD}$ to GND	-0.3 V to +25 V
$V_{SS}$ to GND	+0.3 V to -25 V
Analog, Digital Inputs <sup>2</sup>	$V_{SS} - 0.3\text{ V}$ to $V_{DD} + 0.3\text{ V}$ or 20 mA, Whichever Occurs First
Continuous Current, S or D	30 mA
Peak Current, S or D (Pulsed at 1 ms, 10% Duty Cycle max)	100 mA
Operating Temperature Range	
Industrial (B Version)	-40° C to +85° C
Automotive (Y Version)	-40° C to +125° C
Storage Temperature Range	-65° C to +150° C
Junction Temperature	150° C

Parameter	Rating
TSSOP Package, Power Dissipation	450 mW
$\theta_{JA}$ , Thermal Impedance	150.4° C/W
$\theta_{JC}$ , Thermal Impedance	50° C/W
Lead Temperature, Soldering	
Vapor Phase (60 sec)	215° C
Infrared (15 sec)	220° C

<sup>1</sup> Stresses above those listed under Absolute Maximum Ratings may cause permanent damage to the device. This is a stress rating only; functional operation of the device at these or any other conditions above those listed in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability. Only one absolute maximum rating may be applied at any one time.

<sup>2</sup> Overvoltages at A, EN, S, or D will be clamped by internal diodes. Current should be limited to the maximum ratings given.

**ESD CAUTION**

ESD (electrostatic discharge) sensitive device. Electrostatic charges as high as 4000 V readily accumulate on the human body and test equipment and can discharge without detection. Although this product features proprietary ESD protection circuitry, permanent damage may occur on devices subjected to high energy electrostatic discharges. Therefore, proper ESD precautions are recommended to avoid performance degradation or loss of functionality.



**PIN CONFIGURATIONS - TSSOP**

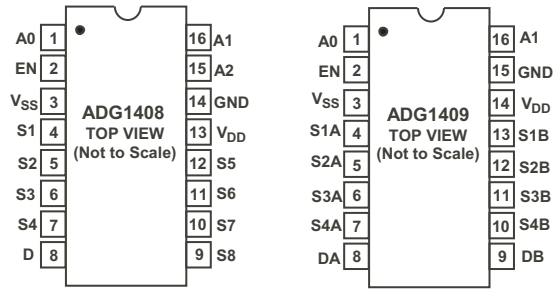


Figure 1. Pin Configurations - TSSOP

Table 5. ADG408 Truth Table

A2	A1	A0	EN	ON SWITCH
X	X	X	0	NONE
0	0	0	1	1
0	0	1	1	2
0	1	0	1	3
0	1	1	1	4
1	0	0	1	5
1	0	1	1	6
1	1	0	1	7
1	1	1	1	8

Table 6. ADG409 Truth Table

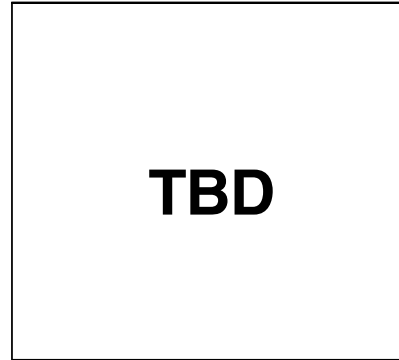
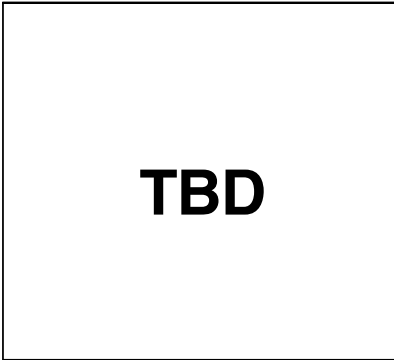
AI	A0	EN	ON SWITCH PAIR
X	X	0	NONE
0	0	1	1
0	1	1	2
1	0	1	3
1	1	1	4



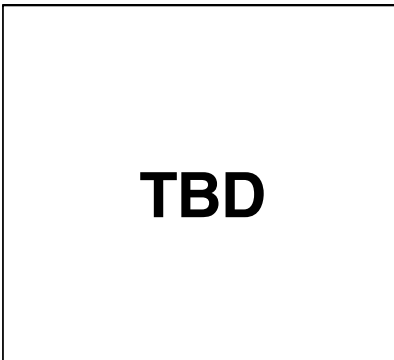
## TERMINOLOGY

$V_{DD}$	Most positive power supply potential.
$V_{SS}$	Most negative power supply potential in dual supplies. In single supply applications, it may be connected to ground.
GND	Ground (0 V) reference.
$R_{ON}$	Ohmic resistance between D and S.
$\Delta R_{ON}$	Difference between the $R_{ON}$ of any two channels.
$I_S$ (OFF)	Source leakage current when the switch is off.
$I_D$ (OFF)	Drain leakage current when the switch is off.
$I_D, I_S$ (ON)	Channel leakage current when the switch is on.
$V_D$ ( $v_s$ )	Analog voltage on terminals D, S.
$C_S$ (OFF)	Channel input capacitance for OFF condition.
$C_D$ (OFF)	Channel output capacitance for OFF condition.
$C_D, C_S$ (ON)	ON switch capacitance.
$C_{IN}$	Digital input capacitance.
$t_{ON}$ (EN)	Delay time between the 50% and 90% points of the digital input and switch ON condition.
$t_{OFF}$ (EN)	Delay time between the 50% and 90% points of the digital input and switch OFF condition.
$t_{TRANSITION}$	Delay time between the 50% and 90% points of the digital inputs and the switch ON condition when switching from one address state to another.
$t_{OPEN}$	OFF time measured between the 80% point of both switches when switching from one address state to another.
$V_{INL}$	Maximum input voltage for Logic 0.
$V_{INH}$	Minimum input voltage for Logic 1.
$I_{INL}$ ( $I_{INH}$ )	Input current of the digital input.
$I_{DD}$	Positive supply current.
$I_{SS}$	Negative supply current.
Off Isolation	A measure of unwanted signal coupling through an OFF channel.
Charge Injection	A measure of the glitch impulse transferred from the digital input to the analog output during switching.
Bandwidth	The frequency at which the output is attenuated by 3dBs.
On Response	The Frequency response of the "ON" switch.
THD + N	The ratio of the harmonic amplitude plus noise of the signal to the fundamental.

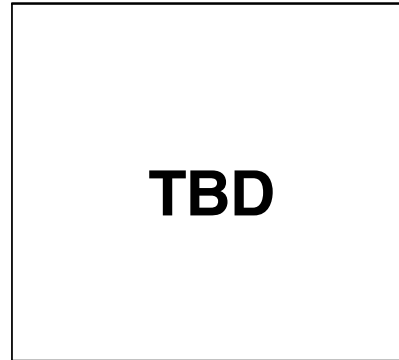
### TYPICAL PERFORMANCE CHARACTERISTICS



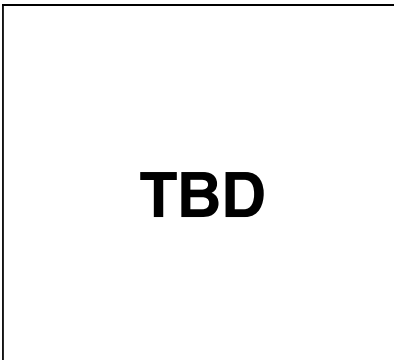
TPC 1. On Resistance as a Function of  $V_D(V_S)$  for Single Supply



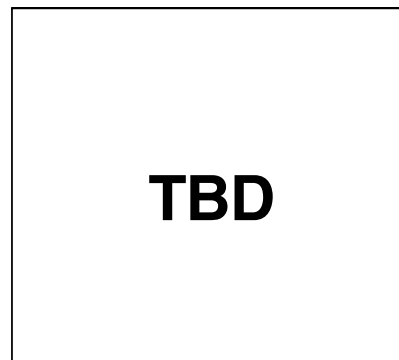
TPC 4. On Resistance as a Function of  $V_D(V_S)$  for Different Temperatures, Single Supply



TPC 2. On Resistance as a Function of  $V_D(V_S)$  for Dual Supply

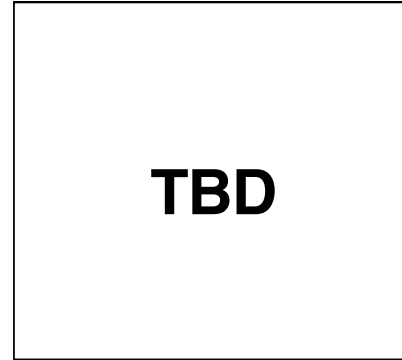
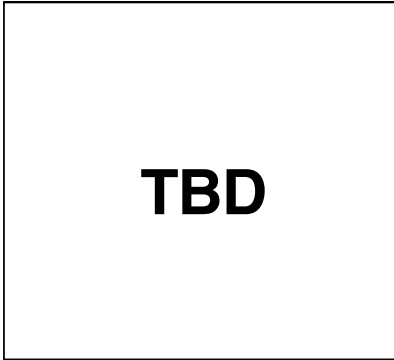


TPC 5. On Resistance as a Function of  $V_D(V_S)$  for Different Temperatures, Dual Supply



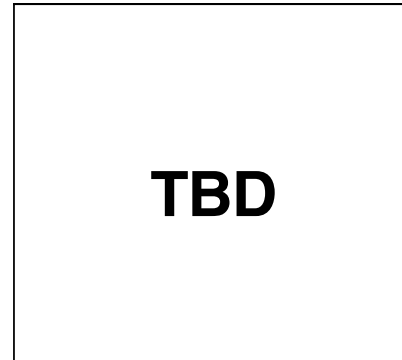
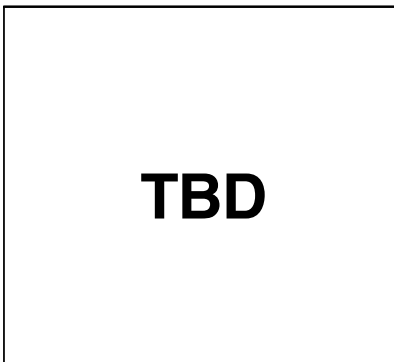
TPC 3. On Resistance as a Function of  $V_D(V_S)$  for Different Temperatures, Single Supply

TPC 6. Leakage Currents as a Function of  $V_b (V_s)$



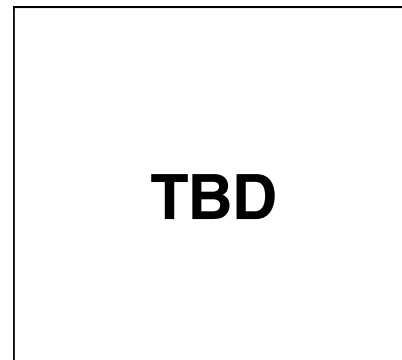
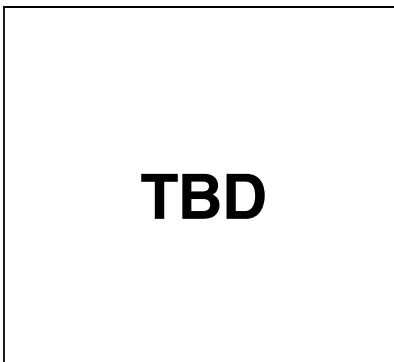
*TPC 10. TON/TOFF Times vs. Temperature)*

*TPC 7. Leakage Currents as a function of Temperature*



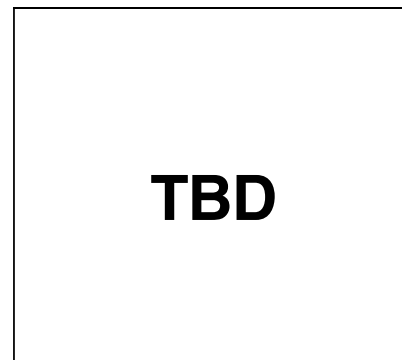
*TPC 8 Supply Currents vs. Input Switching Frequency*

*TPC 11 Off Isolation vs. Frequency*

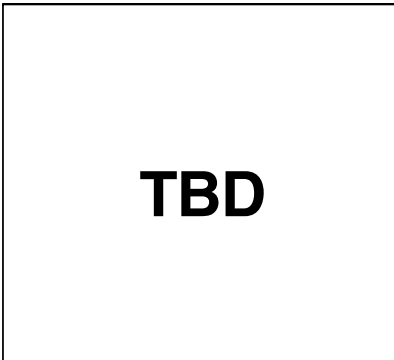


*TPC 9 . Charge Injection vs. Source Voltage*

*TPC 12 Crosstalk vs. Frequency*

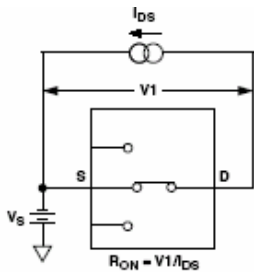


*TPC 13. On Response vs. Frequency*

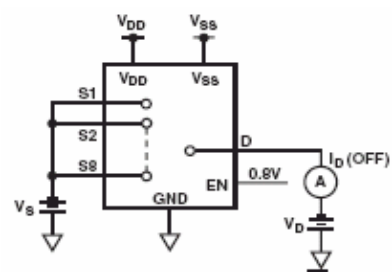


TPC 14. THD + N vs. Frequency

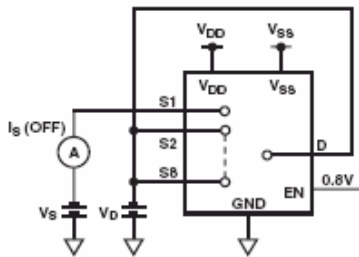
TEST CIRCUITS



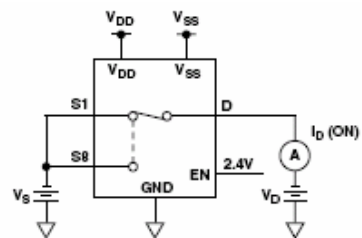
Test Circuit 1. On Resistance  
Figure 2. Test Circuit 1. On Resistance



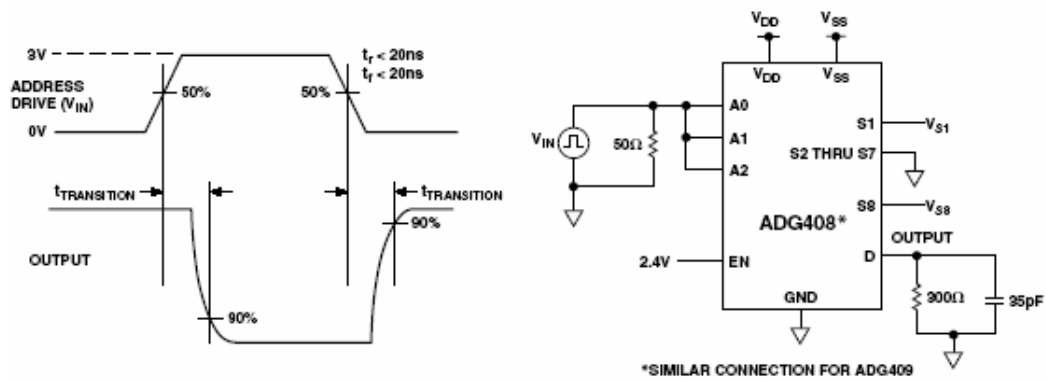
Test Circuit 3. Id (OFF)  
Figure 4. Test Circuit 3. Id (OFF)



Test Circuit 2. Is (OFF)  
Figure 3. Test Circuit 2. Is (OFF)

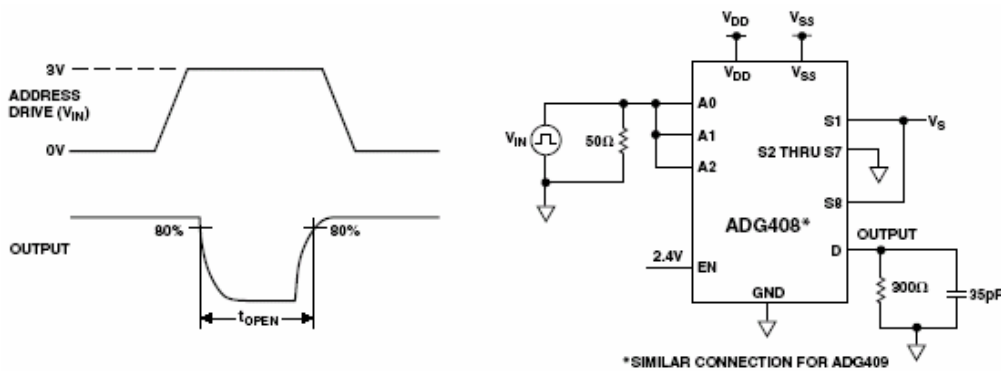


Test Circuit 4. Id (ON)  
Figure 5. Test Circuit 4. Id (ON)



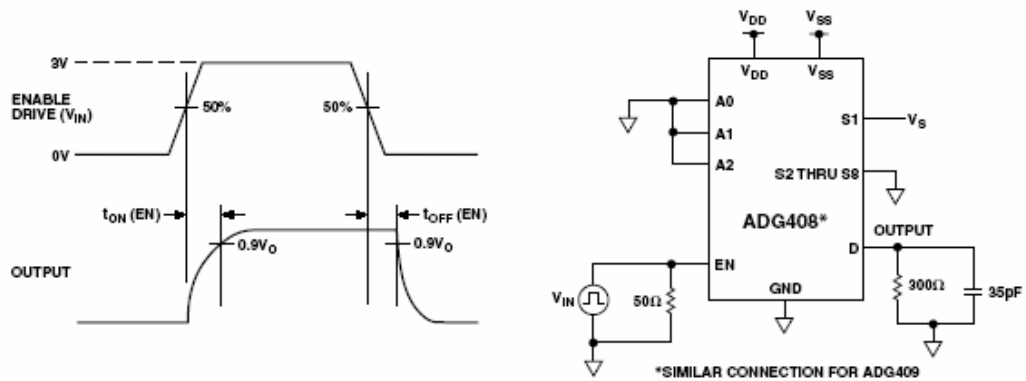
Test Circuit 5. Switching Time of Multiplexer,  $t_{\text{TRANSITION}}$

Figure 6. Test Circuit 5. Switching Time of Multiplexer,  $t_{\text{TRANSITION}}$



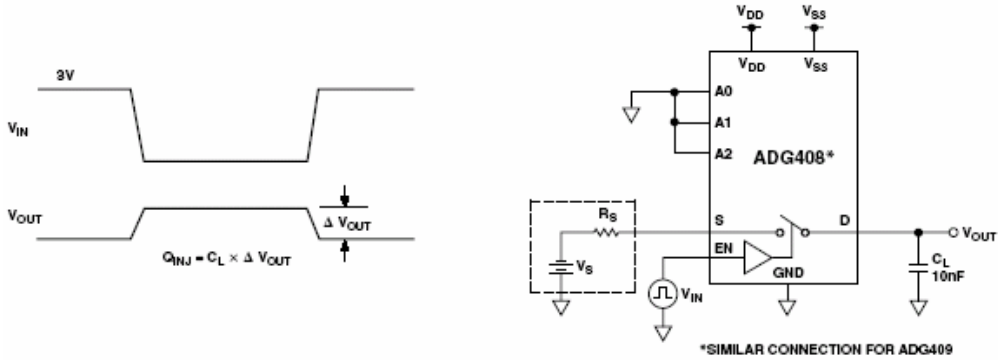
Test Circuit 6. Break-Before-Make Delay,  $t_{\text{OPEN}}$

Figure 7. Test Circuit 6. Break-Before-Make Delay,  $t_{\text{OPEN}}$



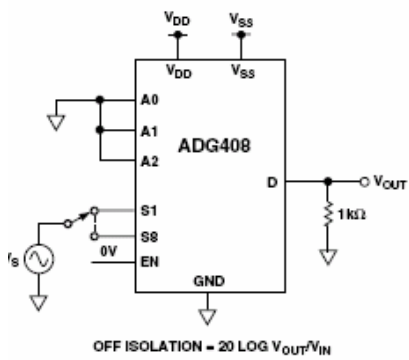
Test Circuit 7. Enable Delay,  $t_{\text{ON}}(\text{EN})$ ,  $t_{\text{OFF}}(\text{EN})$

Figure 8. Test Circuit 7. Enable Delay,  $t_{\text{ON}}(\text{EN})$ ,  $t_{\text{OFF}}(\text{EN})$



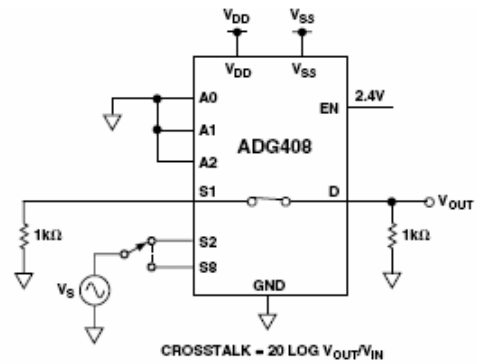
Test Circuit 8. Charge Injection

Figure 9. Test Circuit 8. Charge Injection



Test Circuit 9. OFF Isolation

Figure 10. Test Circuit 9. OFF Isolation



Test Circuit 10. Channel-to-Channel Crosstalk

Figure 11. Test Circuit 10. Channel-to-Channel Crosstalk

## OUTLINE DIMENSIONS

### 16-Lead Thin Shrink Small Outline Package [TSSOP] (RU-16)

Dimensions shown in millimeters

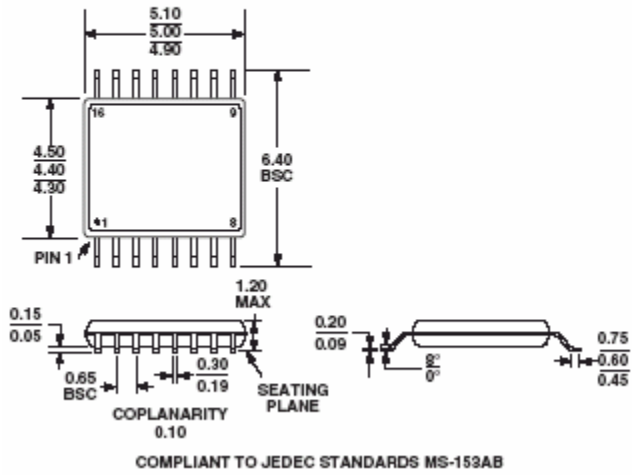


Figure 12. 16-Lead Thin Shrink Small Outline Package [TSSOP] (RU-16)

**ORDERING GUIDE**

<b>Model</b>	<b>Temperature Range</b>	<b>Package Option<sup>1</sup></b>
ADG1408BRU	-40°C to +125°C	RU-16
ADG1409BRU	-40°C to +125°C	RU-16

<sup>1</sup> RU = Thin Shrink Small Outline Package (TSSOP)